

Non-linear Effects in Resonant Tunnelling Through a Quantum Dot

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We study resonant tunnelling transport properties of a quantum dot connected to two leads. The flowing electrons are supposed to interact strongly at the quantum dot. The system is represented by an Anderson impurity Hamiltonian. The transport properties are characterised by the well-known Coulomb blockade properties. However, superimposed to them, this **1D** system possesses novel non-linear current bistability behaviour and other instability phenomena, which leads eventually to chaos.

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INTRODUCTION

Transport properties have been extensively studied due to their interesting device application and very rich phenomenology. Since the first observation of resonant tunnelling in a **3D** double barrier structure by Chang, Esaki and Tsu¹, these devices have been found to present non-linear properties, which are reflected in the observation of multistabilities in the I-V characteristic curve. Besides a peak due to simple resonant transmission, dynamical intrinsic bistability and hysteresis in the negative differential resistance region has been measured^{2,3}. These properties have been explained as a non-linear effect due to the Coulomb interactions among the flowing charges³. The phenomenon can be thought to be produced by the rapid leakage of the electronic charge accumulated at the well between the barriers when the applied potential is just taking the device out of resonance⁴. Very recently we were able to show that the addition of a magnetic field parallel to the current induces self-sustained intrinsic current oscillations in an asymmetric double barrier structure⁵. These oscillations were attributed to the enhancement due to the external magnetic field of the non-linear dynamic coupling of the current to the charge trapped in the well. These results showed that the system bifurcates as the field is increased, and may transit to chaos at large enough fields. Although the presence of the external magnetic field introduces some **1D** character to these systems, all the properties are obtained from **3D** systems. In recent years, electron channels have been fabricated with a lateral quantum confine energy levels sufficiently separated one from the other as to be able to study properties of a **1D** system. When a quantum dot is connected through these electron channels to a battery, the system exhibits pronounced periodic oscillations of the conductance when the state of charge of the dot is modified by changing the gate potential. This is a consequence of the Coulomb blockade of an electron when it tries to go into a quantum island, which

is already occupied by another electron^{6,7}. Although the multistability phenomena found in standard **3D** resonant tunnelling devices have not been detected in **1D** systems where the Coulomb blockade is dominant, it is evident that both phenomena derive from the same Coulomb interaction acting between the flowing charges. In this paper we developed a self-consistent theory of resonant tunnelling in quasi-**1D** systems which predicts that, besides the normal Coulomb blockade behaviour in the region of negative differential resistance, the system develops multistable properties. Moreover we show that, while the phenomena of hysteresis persists, the system bifurcates and is capable of further bifurcations as the gate potential applied to the dot is increased, leading eventually to true chaos. This fact emphasizes the absence of stationary solutions for the current in certain regions of the parameter space, indicating the existence of time-dependent phenomena, probably oscillations.

THE MODEL

A theoretical understanding of these properties should consider that the system is in a non-equilibrium situation under the effect of many-body interactions. A **1D** Anderson Hamiltonian microscopically describes the system where the quantum dot plays the role of the impurity. The leads are represented by a **1D** tight-binding Hamiltonian connecting the dot to two reservoirs characterised by Fermi levels $\mathcal{E}_l$ and $\mathcal{E}_r$. The difference $\mathcal{E}_l - \mathcal{E}_r$ corresponds to the potential drop from left to right along the sample. The nearest-neighbour Hamiltonian can be written as,

$$\mathcal{H} = t \sum_{\langle ij \rangle \sigma} c_{i\sigma}^\dagger c_{j\sigma} + \sum_{i\sigma} \epsilon_i n_{i\sigma} + \mathcal{V}_p n_{o\sigma} + \frac{\mathcal{U}}{2} \sum_{\sigma} n_{o\sigma} n_{o\bar{\sigma}} + t_r \left(c_{o\sigma}^\dagger c_{1\sigma} + c.c. \right) + t_l \left(c_{o\sigma}^\dagger c_{\bar{1}\sigma} + c.c. \right) \quad (1)$$

where $\mathcal{V}_p$ is the external gate which controls the energy of the localised state within the well, $\mathcal{U}$ is the local electronic repulsion of the charges inside the well localized at site 0, t is the nearest-neighbour hopping matrix elements, t_r and t_l are the coupling matrix elements between the well and the right and left contacts. It is assumed the system has N sites. The electron-electron interaction will be treated within the context of the Hubbard approximation⁶, which is adequate to treat the Coulomb blockade and the non-linear effects derived from the Coulomb interaction. However, it will not be capable of describing the low-lying excitations associated to the Kondo effect which in principle the system would have at temperatures below the Kondo temperature. On a tight-binding basis, the stationary state of energy $\mathcal{E}_k$ can be written as

$$\varphi_{k\sigma} = \sum_i a_{i\sigma}^k \phi_{i\sigma}(r) \quad (2)$$

where $\phi_{i\sigma}$ is a Wannier state localized at site i of spin σ and the coefficients $a_{i\sigma}^k$ obey the non-linear difference equations,

$$\left(\epsilon_i - \mathcal{E}_k + 2t \right) a_{i,\sigma}^k = \left(a_{i-1,\sigma}^k + a_{i+1,\sigma}^k \right) t \quad (3)$$

$$\left(\epsilon_o - \mathcal{E}_k + 2t + \mathcal{V}_p + \mathcal{U} \right) a_{o,\sigma}^k =$$

$$a_{-1,\sigma}^k \left(t + \frac{\mathcal{U} t_l n_{\sigma}^-}{-\mathcal{E}_k + 2t + \mathcal{V}_p} \right) + a_{1,\sigma}^k \left(t + \frac{\mathcal{U} t_r n_{\sigma}^-}{-\mathcal{E}_k + 2t + \mathcal{V}_p} \right) ; i = 0 \quad (4)$$

where $n_{\sigma}^- = 1 - \langle n_{o,\sigma} \rangle$ and $\langle n_{o,\sigma} \rangle$ is the number of electrons with spin σ at the well site and is calculated from the tight-binding amplitudes at the well, according to the equation,

$$\langle n_{o,\sigma} \rangle = \sum_{k < k_f^l} |a_{o\sigma}^k|^2 \quad (5)$$

where the sum over k covers all occupied electrons states of the system with energy below the Fermi level, incident from the emitter side. In order to study the solutions of equation [2] we assume a plane wave incident from the left with an intensity I , with a partial reflection amplitude R . The waveform at the far right is a simple plane wave with intensity given by the transmission probability T . Taking this to be the solution at the far right and left edges of the system, we can write,

$$\varphi^k(r) = I e^{ikr} + R e^{-ikr} \quad r \ll 0 \quad (6)$$

$$\varphi^k(r) = T e^{ikr} \quad r \gg L \quad (7)$$

where L is the length of the active part of the system in units of the lattice parameter. The solution of equations

[3,4] can be obtained through an adequate iteration of it from right to left. For a given transmitted amplitude, the associated reflected and incident amplitudes may be determined by matching the iterated function to the proper plane wave at the far left, equation [6]. The transmission square modulus of T , adequately normalised by the incident amplitude I , obtained from the iterative procedure, multiplied by the wave vector k , gives us the contribution of this wave vector to the current. Due to the presence of the non-linear term, the equations [3,4] have to be solved self-consistently. With this purpose, we define a second pseudo-time-like iteration in the following way. Initially Eqs. [3,4] are solved ignoring the non-linear term and for energies up to the Fermi energy. The coefficients thus obtained correspond to a solution for non-interacting electrons. They are used to construct the non-linear term for the next solution. The procedure is continued, using for the non-linear term solutions corresponding to the previous iteration. This procedure defines a spatial-pseudo-temporal map that is linear in space and non-linear in time. Maps non-linear in space and time have been studied in other contexts. In particular, the coupled map model for open flow has been found to exhibit spatial chaos with temporal periodicity⁷. A similar behaviour has been found studying resonant tunnelling properties of a **3D** double barrier devices under the effect of an external magnetic field along the current (4). As we shall show, in our case chaos develops in the iteration of time, as the self-consistent loop is developed.

NUMERICAL RESULTS

We study a model which consists of leads connected to a quantum dot represented by $t_r = 0.1t$, $t_l = 0.1t$, $\mathcal{U} = 1.0t$ and a Fermi level $e_f = 0.05t$. These parameters could adequately represent a semiconductor device constructed from a GaAs substrate. The normalisation of the wave function is taken so that each site could have up to a maximum of two electrons. The map is linear in space so that the normalisation involves a simple multiplication of all coefficients by a constant. Since the electron density has rather long-range oscillations, we made sure the sample was long enough to make finite size effects negligible. This is guaranteed by taking a sample of $N > 100$ sites.

Fig 1 shows the current voltage (I-V) characteristics for several values of the gate potential $\mathcal{V}_p$ applied at the quantum dot. As it is shown in the figure for this **1D** system, we obtain a similar behavior to the very well-known bistability in **3D** systems. There are two solutions for the current as the voltage is increased when the dot is charged (solid line), and as the voltage is decreased when the dot is without charge (stars). In either case, the self-consistent solution converges to a stable fixed point after some finite number of iterations. Similarly to **3D** tunnelling, the choice of an asymmetric structure ($t_r > t_f$)

and an increase of the Fermi level augments the charge content of the well and consequently the non-linearities and in particular the width of the hysteresis loop for this **1D** system. When the gate potential is greater than a threshold value, which depends upon the parameters of the system, a completely novel feature starts to develop where two periods and two fixed points are encountered for certain voltages as shown in Fig 1b. This bubble-like solution is obtained as the voltage is increased outside the region of bistability showing that although both phenomena are derived from the non-linearities introduced by the local Coulomb repulsion, they correspond to two different effects. Note that these new solutions are not reached, as the voltage is decreased (stars) as it corresponds to a discharged dot where the non-linearities are negligible. As the potential gate is raised still further, the area of the bistable bubble increases and it enters into the bistable region. At larger gate potentials the solution undergoes further bifurcations and finally a bifurcation cascade leading to a chaotic region as it is shown in fig1c and 1d for a gate potential $\mathcal{V}_p = -0.7t$ and $-1.4t$ respectively.

As the external applied potential increases still further, the chaotic region eventually unfolds to a solution of finite periodicity or to a unique self-consistent one. In fig.2 a phase diagram in the parameter space $V - \mathcal{V}_p$ shows the various structures we have obtained. The thick lines define the region of bistability, while the stars delimit the region where bifurcations of various orders and chaotic behaviour take place.

CONCLUSIONS

We have shown that a quantum dot connected to two leads and under the effect on an external applied potential have, superimposed to the Coulomb blockade oscillations of the current, bistable solutions and instabilities which eventually become chaotic. Although bistabilities in the current are a well-known phenomenon in **3D** resonant tunneling, to the best of our knowledge, neither its existence has been proposed nor has it been measured in a **1D** system. Bistabilities and general instabilities, although arising from the same Coulomb interaction, appear in different regions of the parameter space reflecting the fact that they are different phenomena. A full-time dependent study of this problem is under way.

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FIG. 1. $I - V$ characteristic curve for a system with $\mathcal{U} = 1t$; $t_r = t_l = 0.1t$ for four different values of the gate potential; a) $\mathcal{V}_p = -0.1t$, b) $\mathcal{V}_p = -0.2t$, c) $\mathcal{V}_p = -0.7t$, d) $\mathcal{V}_p = -1.4t$.

FIG. 2. Phase diagram in the parameter space $V - \mathcal{V}_p$ for the system of Fig1. The thick lines and stars delimit the region of bistability and instability respectively.

